

N-channel 80V 6.9mΩ standard level MOSFET in D2PAK Rev. 2 — 2 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Quick reference data					
Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{1}$	<u>[1]</u> -	-	100	А
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	210	W
junction temperature		-55	-	175	°C
aracteristics					
drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	5.9	6.9	mΩ
characteristics					
gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 40 V;	-	16	-	nC
total gate charge	see Figure 14; see Figure 15	-	71	-	nC
e ruggedness					
non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \ I_{D} = 49 \text{ A}; \\ V_{sup} \leq 80 \text{ V}; \ R_{GS} = 50 \ \Omega; \ unclamped \end{array}$	-	-	700	mJ
	Parameter drain-source voltage drain current total power dissipation junction temperature aracteristics drain-source on-state resistance characteristics gate-drain charge total gate charge e ruggedness non-repetitive drain-source	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source voltage & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C \\ \hline drain current & T_{mb} = 25 \ ^\circ C; \ V_{GS} = 10 \ V; \ see \ Figure 1 \\ \hline total power dissipation & T_{mb} = 25 \ ^\circ C; \ see \ Figure 2 \\ \hline junction temperature \\ \hline aracteristics \\ \hline drain-source on-state & V_{GS} = 10 \ V; \ I_D = 15 \ A; \ T_j = 25 \ ^\circ C; \\ see \ Figure 13 \\ \hline characteristics \\ \hline gate-drain charge & V_{GS} = 10 \ V; \ I_D = 25 \ A; \ V_{DS} = 40 \ V; \\ total gate charge & v_{GS} = 10 \ V; \ I_D = 25 \ A; \ V_{DS} = 40 \ V; \\ see \ Figure 14; \ see \ Figure 15 \\ \hline e \ ruggedness \\ \hline non-repetitive & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^\circ C; \ I_D = 49 \ A; \\ V_{sup} \le 80 \ V; \ R_{GS} = 50 \ \Omega; \ unclamped \\ \hline \end{tabular}$	ParameterConditionsMindrain-source voltage $T_j \ge 25 \ ^\circ$ C; $T_j \le 175 \ ^\circ$ C-drain current $T_{mb} = 25 \ ^\circ$ C; $V_{GS} = 10 \ V$; see Figure 1[1]total power dissipation $T_{mb} = 25 \ ^\circ$ C; see Figure 2-junction temperature-55aracteristics-drain-source on-state $V_{GS} = 10 \ V$; $I_D = 15 \ A$; $T_j = 25 \ ^\circ$ C; see Figure 13characteristics-gate-drain charge $V_{GS} = 10 \ V$; $I_D = 25 \ A$; $V_{DS} = 40 \ V$; total gate charge-e ruggedness-non-repetitive $V_{GS} = 10 \ V$; $T_{j(init)} = 25 \ ^\circ$ C; $I_D = 49 \ A$; $V_{sup} \le 80 \ V$; $R_{GS} = 50 \ \Omega$; unclamped-	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min & Typ \\ \hline drain-source voltage & T_j \ge 25 \ ^{\circ}C; \ T_j \le 175 \ ^{\circ}C & - & - \\ \hline drain current & T_{mb} = 25 \ ^{\circ}C; \ V_{GS} = 10 \ V; \ see \ Figure 1 & 1 & - & - \\ \hline total power dissipation & T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 2 & - & - \\ \hline junction temperature & -55 & - \\ \hline aracteristics & & & & & & & \\ \hline drain-source on-state & V_{GS} = 10 \ V; \ I_D = 15 \ A; \ T_j = 25 \ ^{\circ}C; & & & & & & & \\ \hline drain-source on-state & V_{GS} = 10 \ V; \ I_D = 15 \ A; \ T_j = 25 \ ^{\circ}C; & & & & & & & \\ \hline characteristics & & & & & & & & \\ \hline characteristics & & & & & & & & \\ \hline characteristics & & & & & & & & \\ \hline drain charge & V_{GS} = 10 \ V; \ I_D = 25 \ A; \ V_{DS} = 40 \ V; & & & & & & & 16 \\ \hline total gate charge & & & & & & & & & \\ \hline e ruggedness & & & & & & & & \\ \hline non-repetitive & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \ I_D = 49 \ A; \\ V_{sup} \le 80 \ V; \ R_{GS} = 50 \ \Omega; \ unclamped & & & & & & & & \\ \hline \end{tabular}$	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 ^\circ$ C; $T_j \le 175 ^\circ$ C80drain current $T_{mb} = 25 ^\circ$ C; $V_{GS} = 10 ^\circ$ V; see Figure 111100total power dissipation $T_{mb} = 25 ^\circ$ C; see Figure 2210junction temperature-55-175aracteristics5.96.9characteristicsV_{GS} = 10 V; I_D = 15 A; T_j = 25 ^\circC; see Figure 13-5.96.9characteristicsV_{GS} = 10 V; I_D = 25 A; V_{DS} = 40 V;16-gate-drain chargeV_{GS} = 10 V; I_D = 25 A; V_{DS} = 40 V; -16-total gate chargeV_{GS} = 10 V; T_j(init) = 25 ^\circC; I_D = 49 A; -71-non-repetitive drain-sourceV_{GS} = 10 V; T_j(init) = 25 ^\circC; I_D = 49 A;700

[1] Continuous current rating is limited by package.

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R5-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4.Limiting values

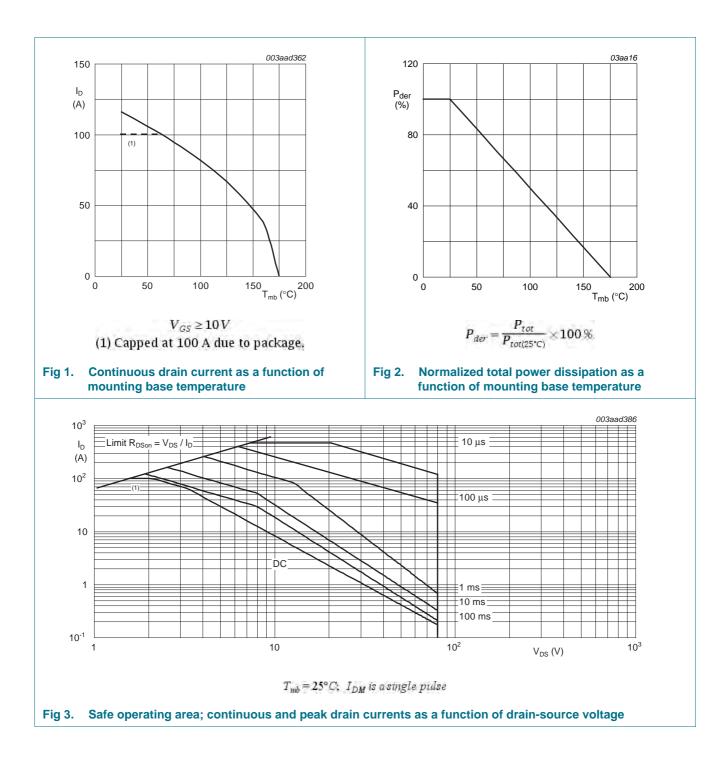
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	82	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	470	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	210	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-d	rain diode				
ls	source current	T _{mb} = 25 °C	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	470	А
Avalanch	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 49 A; V_{sup} \leq 80 V; R_{GS} = 50 Ω ; unclamped	-	700	mJ

[1] Continuous current rating is limited by package.

PSMN6R5-80BS

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5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.4	0.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

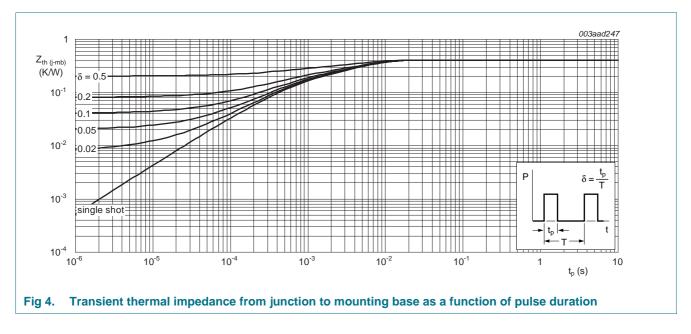


Table 5. Thermal characteristics

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS} drain-source		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	73	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10; see Figure 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10; see Figure 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	2.3	3	4	V
DSS	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	11.5	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	-	16.56	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	5.9	6.9	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.75	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	61	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	71	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	19	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	13.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.8	-	nC
Q _{GD}	gate-drain charge		-	16	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 15}{100000000000000000000000000000000000$	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4461	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	410	-	pF
C _{rss}	reverse transfer capacitance		-	214	-	pF
d(on)	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.5 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	26	-	ns
tr	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	57	-	ns
	fell times		_	22		-
t _f	fall time		-	22	-	ns

Symbol

Source-drain diode

PSMN6R5-80BS

Typ

Max

Unit

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Min

V_{SD} source-drain voltage $I_{S} = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_{i} = 25 \text{ °C};$ 0.79 1.2 V see Figure 17 $I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ t_{rr} reverse recovery time 48 -ns $V_{DS} = 40 V$ recovered charge 82 nC Qr --003aad440 003aad442 100 100 20 5.5 I_D I_{D} -5 (A) (A) 6 80 80 60 60 40 40 $V_{GS}(V) = 4.5$ T_i = 175 °C 20 20 T_i = 25 °C 0 0 1.5 _{VDS} (V) 0 0.5 1 2 0 2 6 4 V_{GS} (V) $T_{j} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ $V_{DS} = 15V$ Output characteristics: drain current as a Transfer characteristics: drain current as a Fig 5. Fig 6. function of drain-source voltage; typical values function of gate-source voltage; typical values 003aad446 003aad447 7000 150 g_{fs} С Ciss (pF) (S) 6000 120 5000 90 C. 4000 60 3000 30 2000 0 0 5 10 15 20 25 V_{GS} (V) 0 20 40 60 80 100 I_D (A) $V_{DS} = 0V; f = 1MHz$ $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ Fig 7. Input and reverse transfer capacitances as a Fig 8. Forward transconductance as a function of function of gate-source voltage; typical values drain current; typical values

Table 6. Characteristics ... continued

Parameter

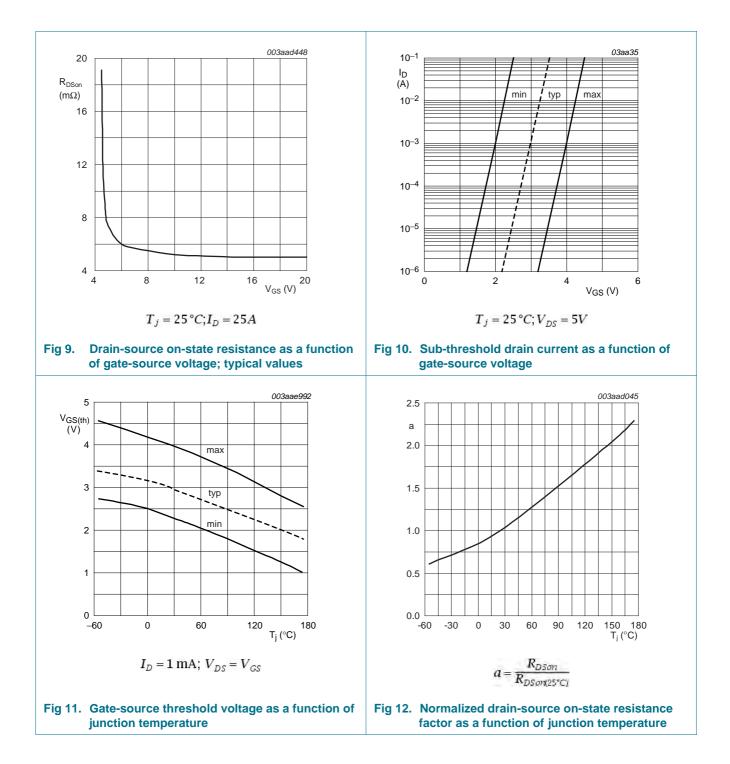
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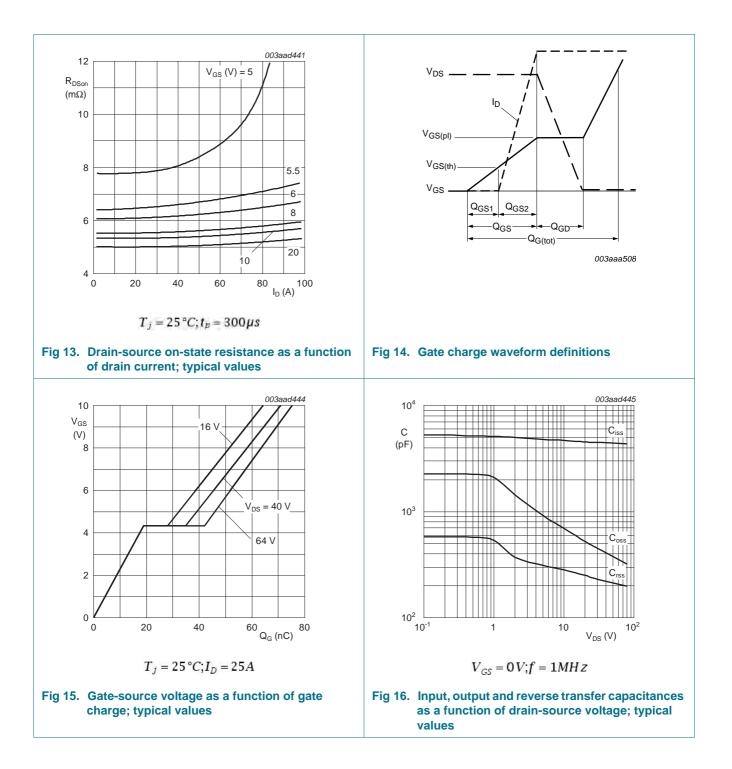
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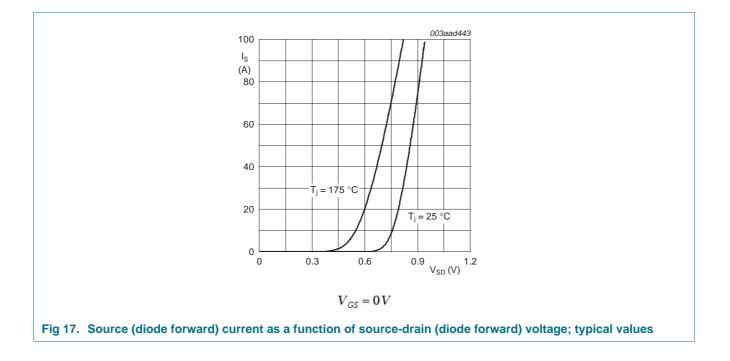
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N-channel 80V 6.9mΩ standard level MOSFET in D2PAK

7. Package outline

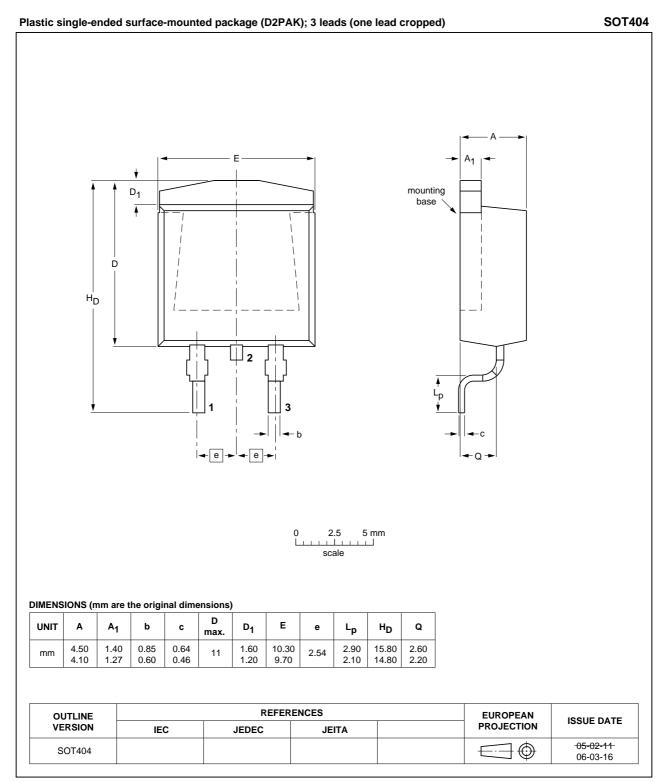


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R5-80BS v.2	20120302	Product data sheet	-	PSMN6R5-80BS v.1
Modifications:	 Status changed 	from objective to product.		
	 Various change 	es to content.		
PSMN6R5-80BS v.1	20111021	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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